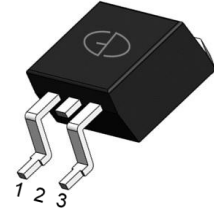


## N-Channel 40V (D-S) Power MOSFET

### Features

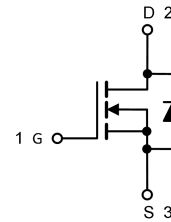
- 100% Avalanche Tested
- Extremely Low Losses with Low FOM  $R_{ds(on)} \cdot Q_g$
- Halogen Free, Pb-Free
- RoHS Compliant



TO-263AB (D<sup>2</sup>PAK)

### Applications

- DC/DC
- Motors, lamps
- Power switching



### Absolute Maximum Ratings ( $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain Source Voltage	$V_{DS}$	60	V
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current, Continuous $V_{GS}=10\text{V}$ (Note 1)	$I_D$	80	A
$T_C=25^\circ\text{C}$			
Drain Current, Pulsed (Note 2)	$I_{DM}$	320	A
Single Avalanche Energy	$E_{AS}$	410	mJ
Power Dissipation (Note 3)	$P_D$	108	W
$T_C=25^\circ\text{C}$			
Operating Junction/ Storage Temperature Range	$T_J / T_{STG}$	-55 to +150	$^\circ\text{C}$

Note 1: Calculated continuous current based on maximum allowable junction temperature.

Note 2: Repetitive rating; pulse width limited by max. junction temperature.

### Thermal Characteristics

Parameter	Symbol	Max	Unit
Thermal Resistance Junction to Case (Note 3)	$R_{thJC}$	1.4	$^\circ\text{C/W}$

Note 3: The power dissipation  $P_D$  is based on max. junction temperature, using junction-to-case thermal resistance.

Electrical Characteristics (T <sub>J</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	--	--	1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA	2	--	4	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	--	--	±100	nA
Drain-Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	--	5.8	8	mΩ
Total Gate Charge	Q <sub>g</sub>	I <sub>D</sub> = 30A, V <sub>DS</sub> =30V, V <sub>GS</sub> = 15V	--	71.2	--	nC
Gate Source Charge	Q <sub>gs</sub>		--	16.4	--	
Gate Drain Charge	Q <sub>gd</sub>		--	23.3	--	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, R <sub>GEN</sub> =3Ω, I <sub>D</sub> = 30A	--	18.8	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	11.8	--	
Turn-off Delay Time	t <sub>d(off)</sub>		--	107.3	--	
Turn-off Fall Time	t <sub>f</sub>		--	58.4	--	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =50V, f=1MHz	--	3934	--	pF
Output Capacitance	C <sub>oss</sub>		--	209	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	191	--	

Reverse Diode Characteristics (T <sub>J</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	I <sub>S</sub>	T <sub>C</sub> =25°C	--	--	80	A
Pulsed Source Current (Body Diode)	I <sub>SM</sub>		--	--	320	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =30A, V <sub>GS</sub> =0V	--	0.89	1.2	V
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> =30A, di/dt = 100 A/μs	--	31.4	--	ns
Reverse Recovery Charge	Q <sub>rr</sub>		--	31.1	--	nC

## Typical Characteristics Curves ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig.1 - Typical Output Characteristics

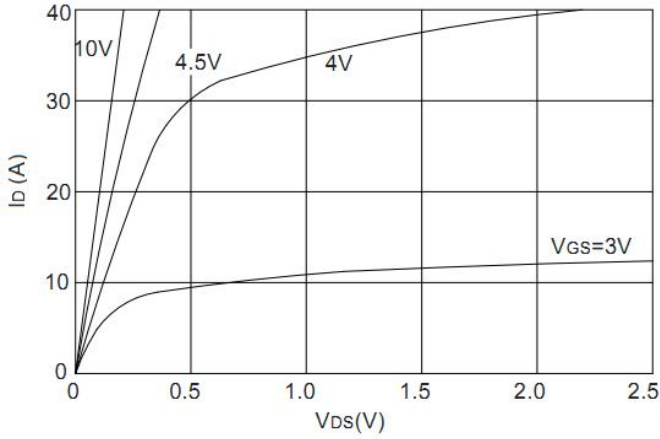


Fig.2 - Transfer Characteristics

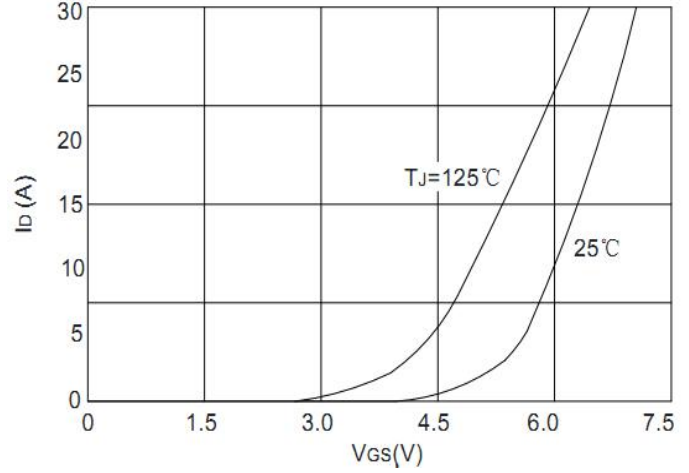


Fig.3 - Gate to Source Cut-off Voltage

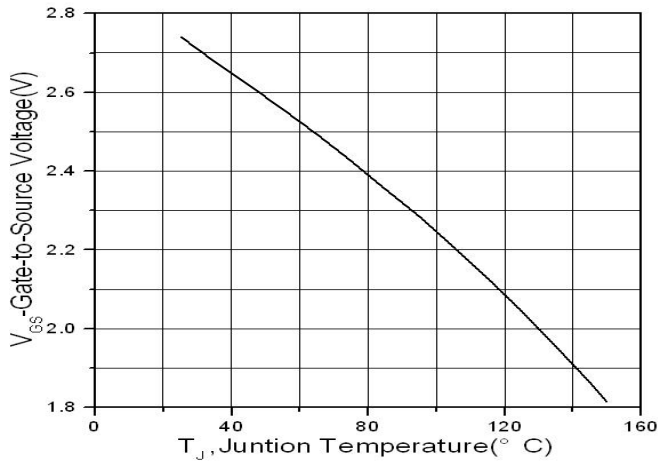


Fig.4 - Body Diode Characteristics

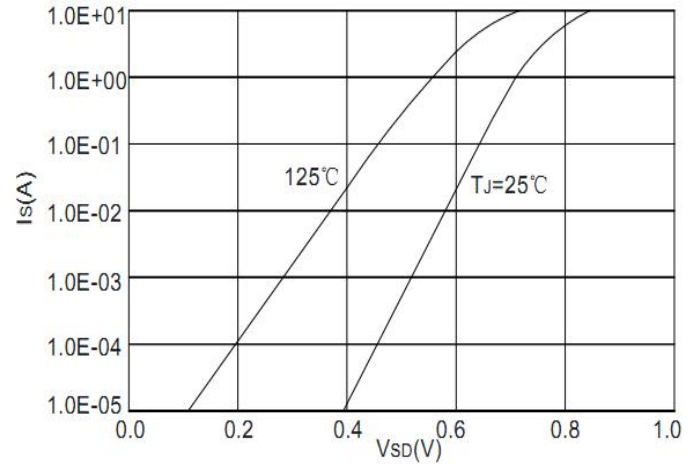


Fig.5 - Gate Charge

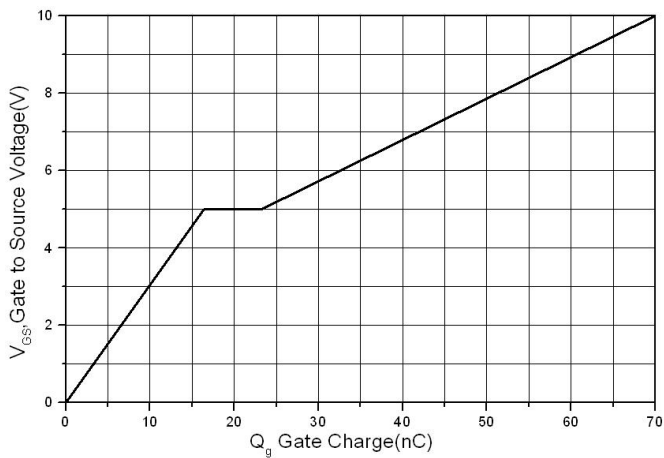
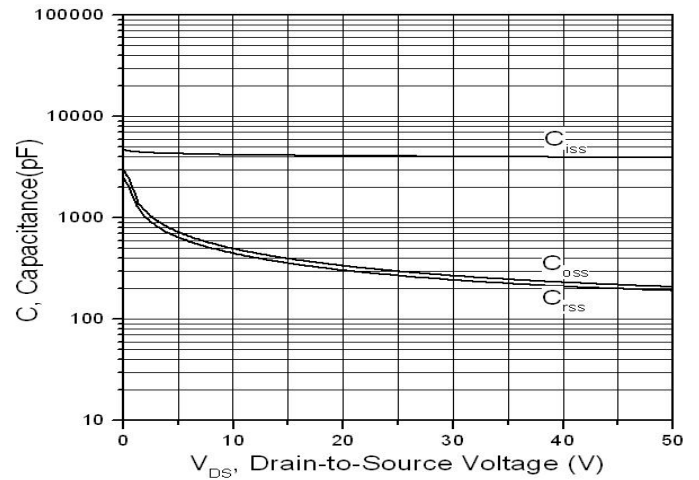


Fig.6 - Capacitance



## Typical Characteristics Curves ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig.7 - Drain-to-Source Breakdown Voltage vs. Temperature

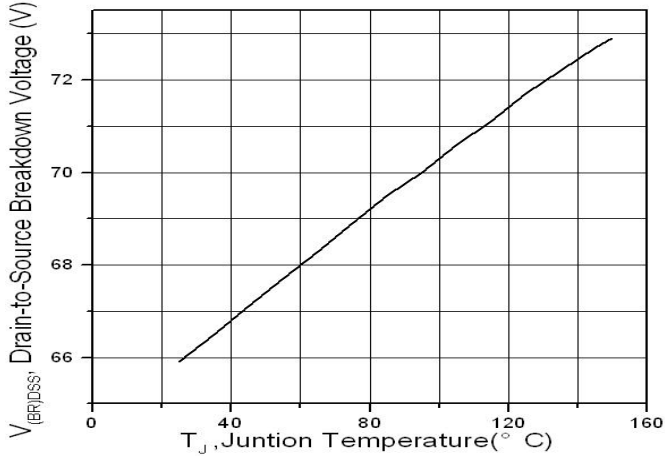


Fig.8 - Normalized On-Resistance vs. Junction Temperature

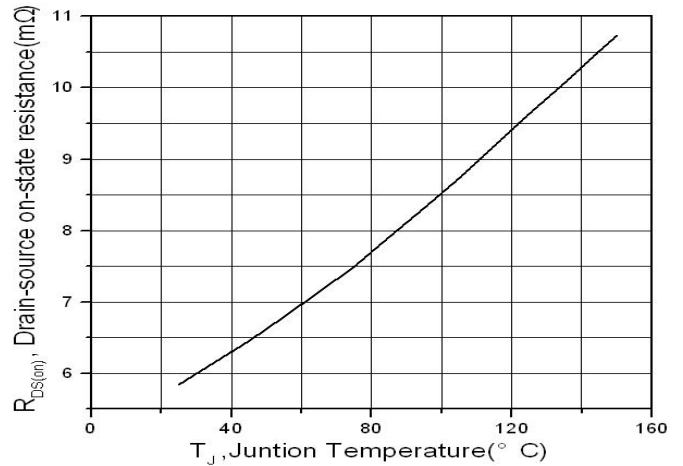


Fig.9 - Safe Operating Area

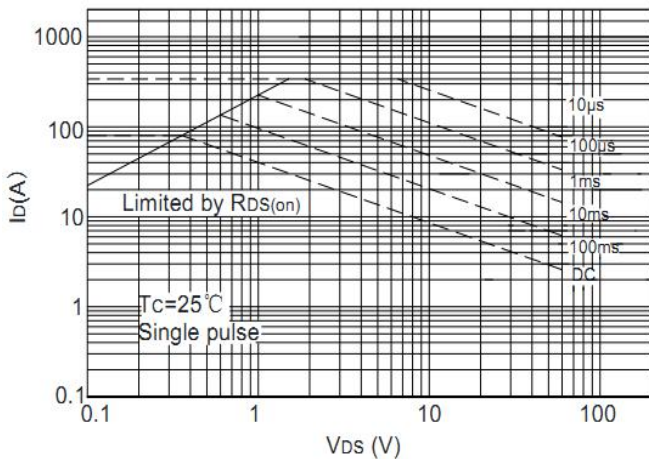


Fig.10 - Drain Current vs. Case Temperature

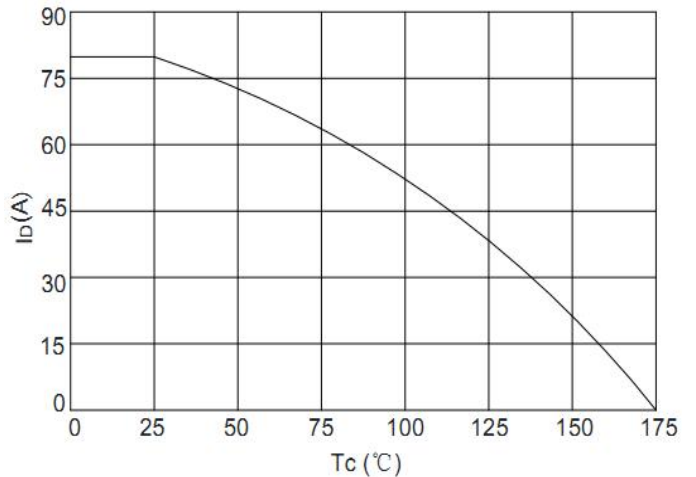
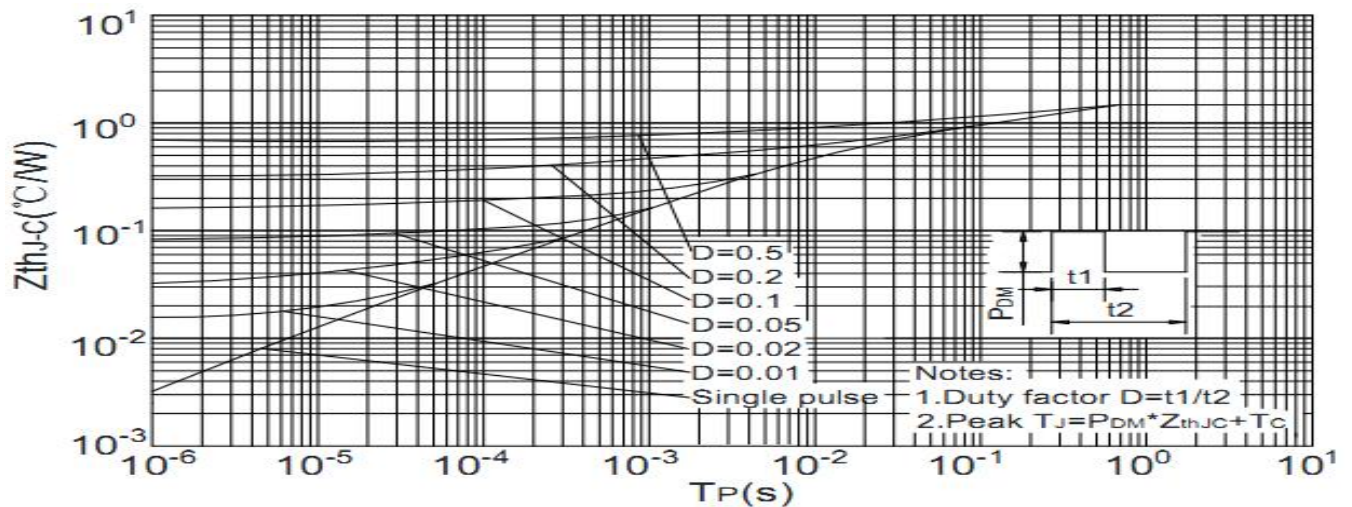


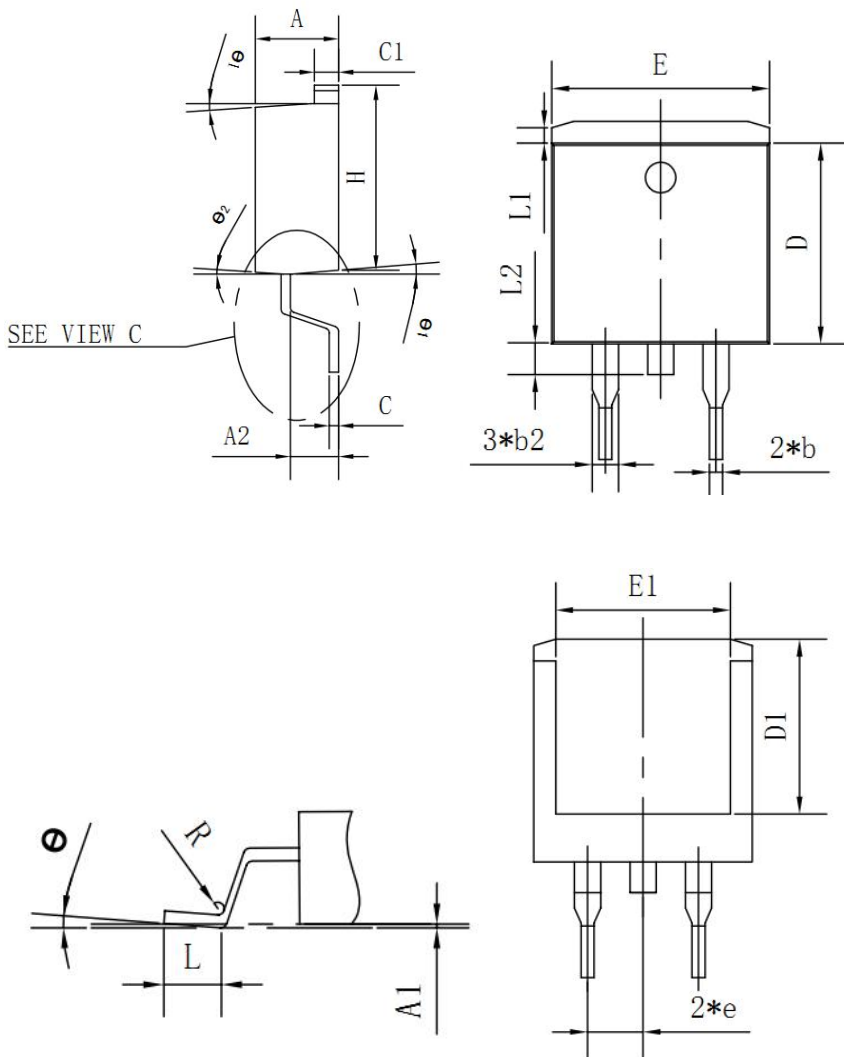
Fig.11 - Normalized Maximum Transient Thermal Impedance



**Package Outline Dimensions** (Unit: millimeters)

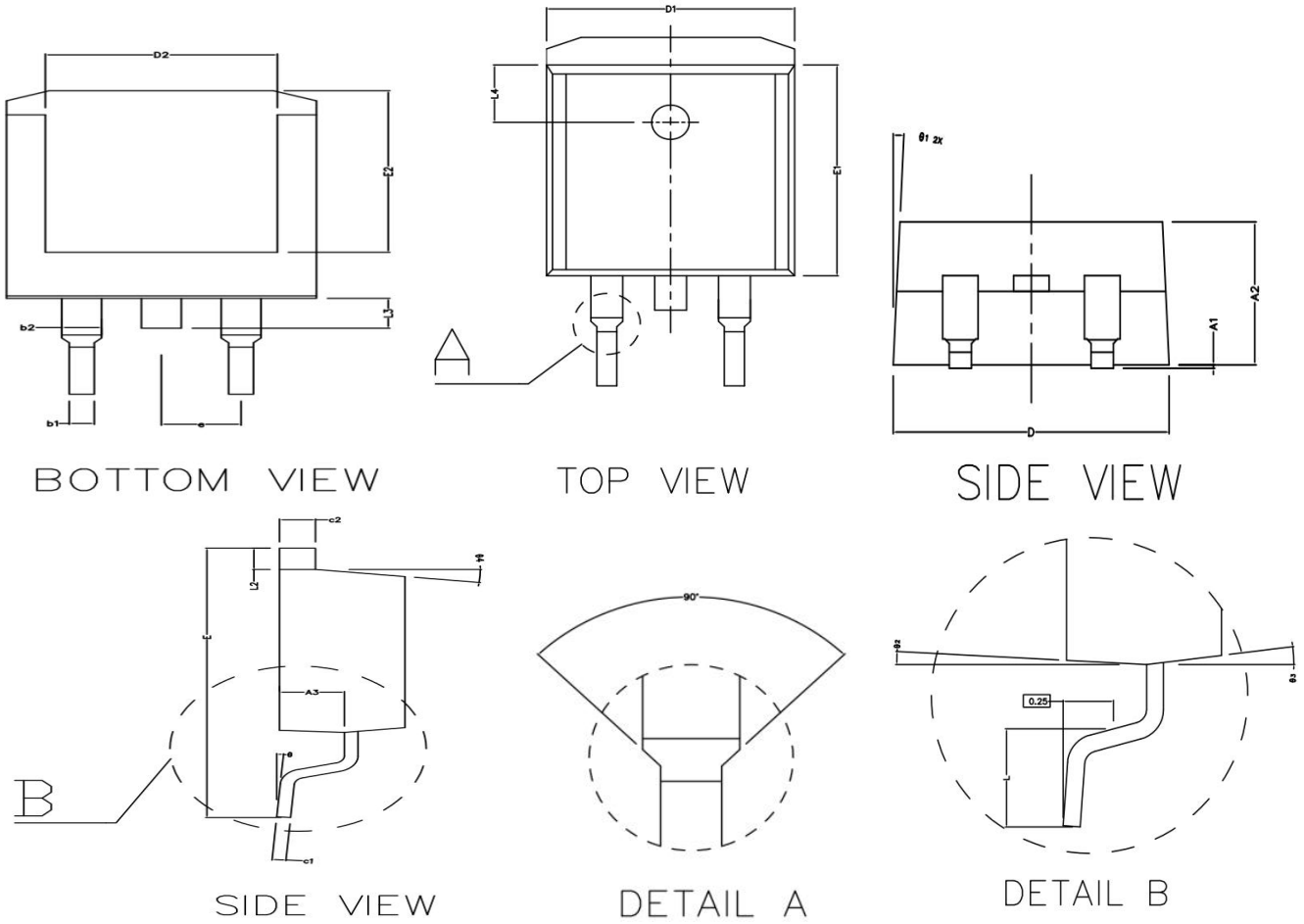
**TO-263**

**Option 1**



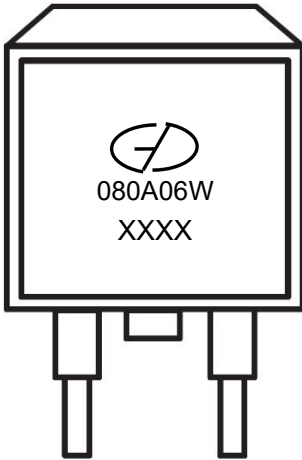
SYMBOL	MIN	NOM	MAX
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.50
b	0.70	0.80	1.00
b2	1.25	1.36	1.38
C	0.45	0.50	0.55
C1	1.29	1.30	1.31
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
$\theta$	0°	4°	8°
$\theta_1$	4°	7°	10°
$\theta_2$	0°	3°	6°

## Option 2




	MIN	NORMAL	MAX
A1	0.020	-	0.200
A2	4.470	4.570	4.670
A3	2.300	2.350	2.400
b1	0.750	-	0.850
b2	1.220	-	1.320
c1	0.500	-	0.550
c2	1.300	-	1.350
D	9.780	9.880	9.980
D1	9.880REF		
D2	7.400REF		
E	14.900	15.100	15.300
E1	9.100	9.200	9.300
E2	8.100REF		
e	2.540REF		
L	2.100	2.300	2.500
L2	1.025		1.375
L3	1.300	1.500	1.700
L4	2.400	2.500	2.600
$\theta_1$	3° TYPE		
$\theta_2$	3° TYPE		
$\theta_3$	7° TYPE		
$\theta_4$	7° TYPE		
$\theta$	0 ~ 8°		

## Marking Outline



Part Name: GMN080A06W

1. Logo Mark: 
2. P/N Mark: 080A06W
3. Date Code: XXXX



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